Yingxin Guan

List of Publications by Year in descending order

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21 papers	307 citations	1040056 9 h-index	839539 18 g-index
21 all docs	21 docs citations	21 times ranked	572 citing authors

#	Article	IF	Citations
1	Atomic Layer Deposition of Al₂O₃â€“Ga₂O₃ Alloy Coatings for Li[Ni_{0.5}Mn_{0.3}Co_{0.2}]O₂ Cathode to Improve Rate Performance in Li-Ion Battery. ACS Applied Materials & Interfaces, 2016, 8, 10572-10580.	8.0	51
2	Enhanced Activity and Stability of TiO₂-Coated Cobalt/Carbon Catalysts for Electrochemical Water Oxidation. ACS Catalysis, 2015, 5, 3463-3469.	11.2	48
3	Radiation-induced segregation in a ceramic. Nature Materials, 2020, 19, 992-998.	27.5	47
4	Self-limiting growth when using trimethyl bismuth (TMBi) in the metal-organic vapor phase epitaxy (MOVPE) of GaAs1â^'yBiy. Journal of Crystal Growth, 2014, 395, 38-45.	1.5	31
5	GaAs1â^'yâ^'zPyBiz, an alternative reduced band gap alloy system lattice-matched to GaAs. Applied Physics Letters, 2014, 105, .	3.3	23
6	Distinct Nucleation and Growth Kinetics of Amorphous SrTiO₃ on (001) SrTiO₃ and SiO₂/Si: A Step toward New Architectures. ACS Applied Materials & Interfaces, 2017, 9, 41034-41042.	8.0	17
7	The Effect of the Bi Precursors, (CH₃)₃Bi and (C₂H₅)₃Bi, on the Metalâ€Organic Vapor Phase Epitaxy of GaAs_{1â€y}Bi_y Films. Chemical Vapor Deposition, 2015, 21, 166-175.	1.3	15
8	Annealing-induced precipitate formation behavior in MOVPE-grown GaAs_{1â^'x}Bi_xexplored by atom probe tomography and HAADF-STEM. Nanotechnology, 2017, 28, 215704.	2.6	14
9	Characteristics of OMVPE grown GaAsBi QW lasers and impact of post-growth thermal annealing. Journal of Applied Physics, 2018, 123, .	2.5	13
10	Tungsten hexacarbonyl and hydrogen peroxide as precursors for the growth of tungsten oxide thin films on titania nanoparticles. AICHE Journal, 2014, 60, 1278-1286.	3.6	9
11	High-Ge-Content SiGe Alloy Single Crystals Using the Nanomembrane Platform. ACS Applied Materials & Interfaces, 2020, 12, 20859-20866.	8.0	7
12	Thermodynamic stability analysis of Bi-containing III-V quaternary alloys and the effect of epitaxial strain. Journal of Physics and Chemistry of Solids, 2020, 138, 109245.	4.0	6
13	Atom probe tomography evidence for uniform incorporation of Bi across the growth front in GaAs1â^'Bi /GaAs superlattice. Journal of Crystal Growth, 2016, 446, 27-32.	1.5	5
14	Single junction solar cell employing strain compensated GaAs0.965Bi0.035/GaAs0.75P0.25 multiple quantum wells grown by metal organic vapor phase epitaxy. Applied Physics Letters, 2018, 112, .	3.3	5
15	Surface kinetics study of metal-organic vapor phase epitaxy of GaAs 1â^'y Bi y on offcut and mesa-patterned GaAs substrates. Journal of Crystal Growth, 2017, 464, 39-48.	1.5	4
16	Impact of thermal annealing on internal device parameters of GaAs _{0.965} Bi _{0.035} /GaAs _{0.75} P _{0.25} quantum well lasers. IET Optoelectronics, 2019, 13, 12-16.	3.3	4
17	Enhanced Incorporation of P into Tensile-Strained GaAs1-yPyLayers Grown by Metal-Organic Vapor Phase Epitaxy at Very Low Temperatures. ECS Journal of Solid State Science and Technology, 2016, 5, P183-P189.	1.8	3
18	Highly tin doped GaAs at low growth temperatures using tetraethyl tin by metal organic vapor phase epitaxy. Journal of Crystal Growth, 2019, 507, 255-259.	1.5	3

#	Article	IF	Citations
19	Reduction of Interface Reactions in the Low-Temperature Solid-Phase Epitaxy of ScAlMgO4 on Al2O3(0001). Crystal Growth and Design, 2020, 20, 6001-6007.	3.0	2
20	Unexpected Bismuth Concentration Profiles in MOVPE GaAs1-xBix Films Revealed by HAADF STEM Imaging. Microscopy and Microanalysis, 2014, 20, 196-197.	0.4	0
21	Metal-organic vapor phase epitaxy of the quaternary metastable alloy In1â€“xGaxAs1â^'yBiy and its kinetics of growth. Journal of Crystal Growth, 2020, 538, 125611.	1.5	0